

FIG. 1 (PRIOR ART)

Hogan & Hartson 81790.0298 Koji HOSONO et al. Semiconductor Device EV 325 217 488 US 8 Drawing Sheets; Sheet 2 of 8

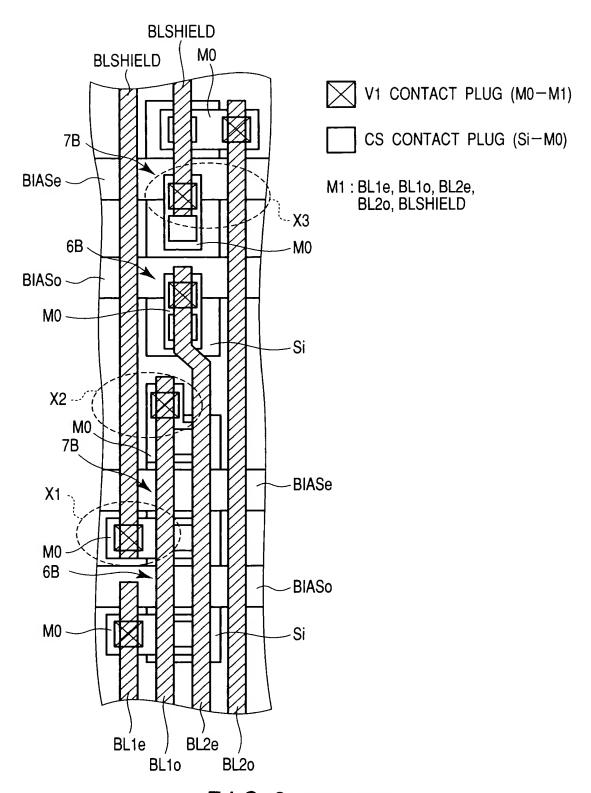
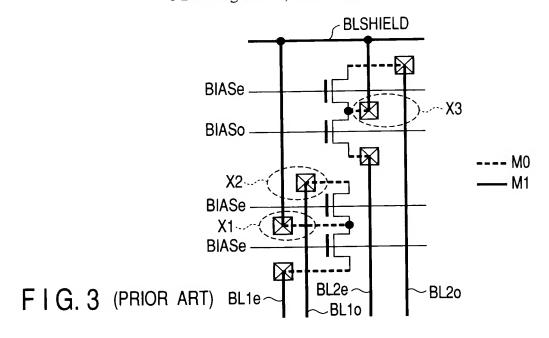
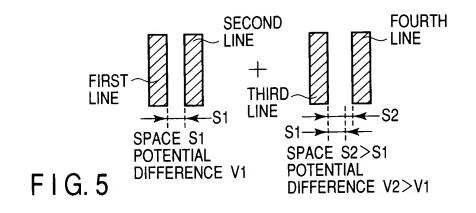
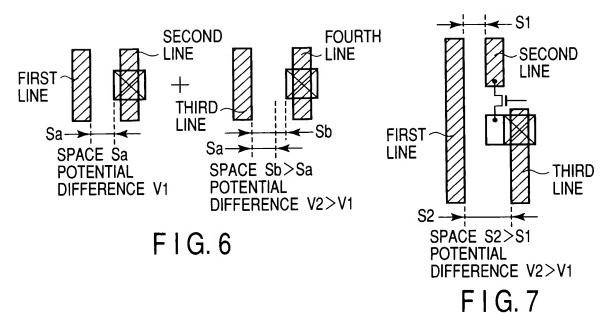


FIG. 2 (PRIOR ART)

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## TIMMING OF ERASE OPERATION

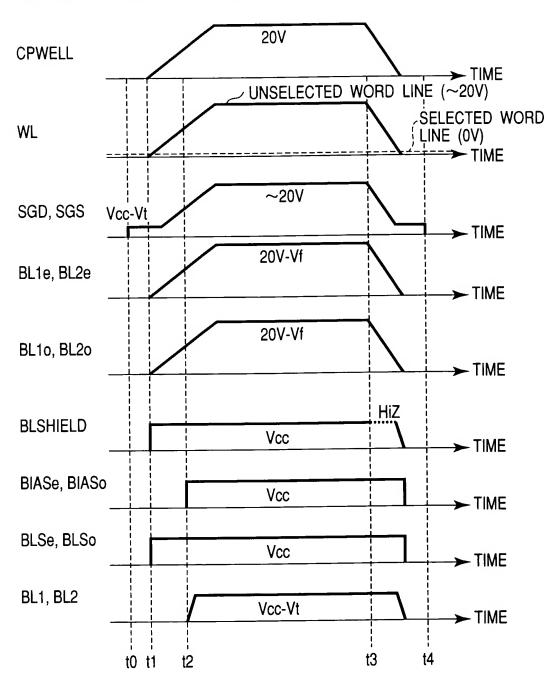
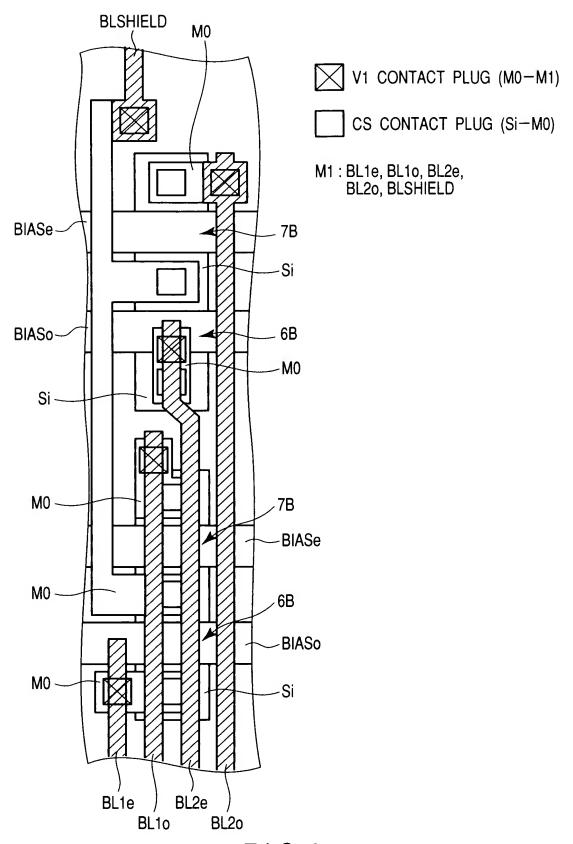


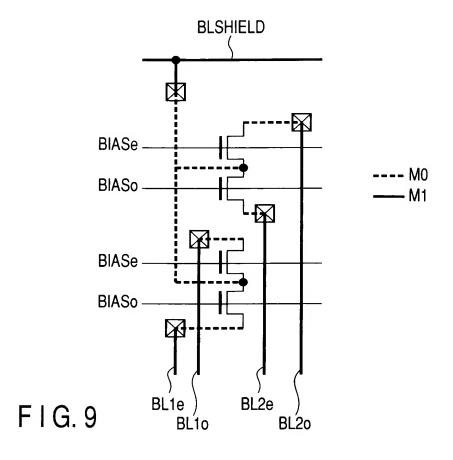
FIG. 4 (PRIOR ART)

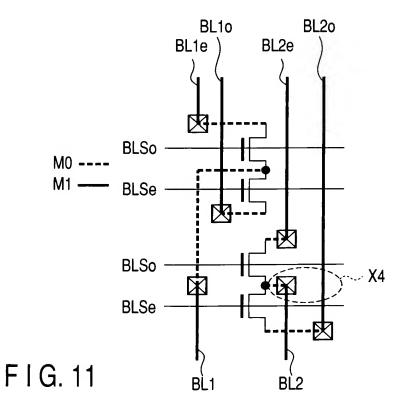
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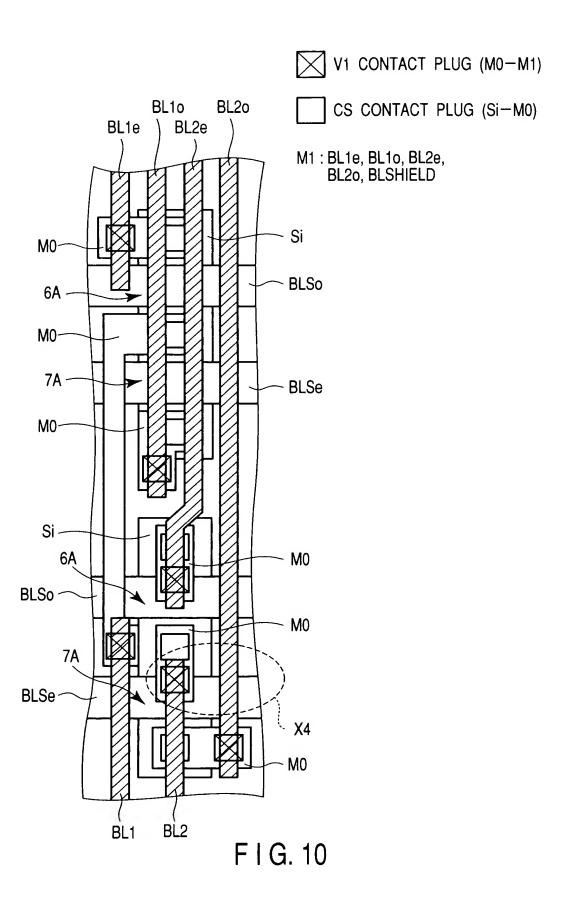
F I G. 8

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